

TSTE05 Elektronik & mätteknik

Föreläsning 12

Dioder

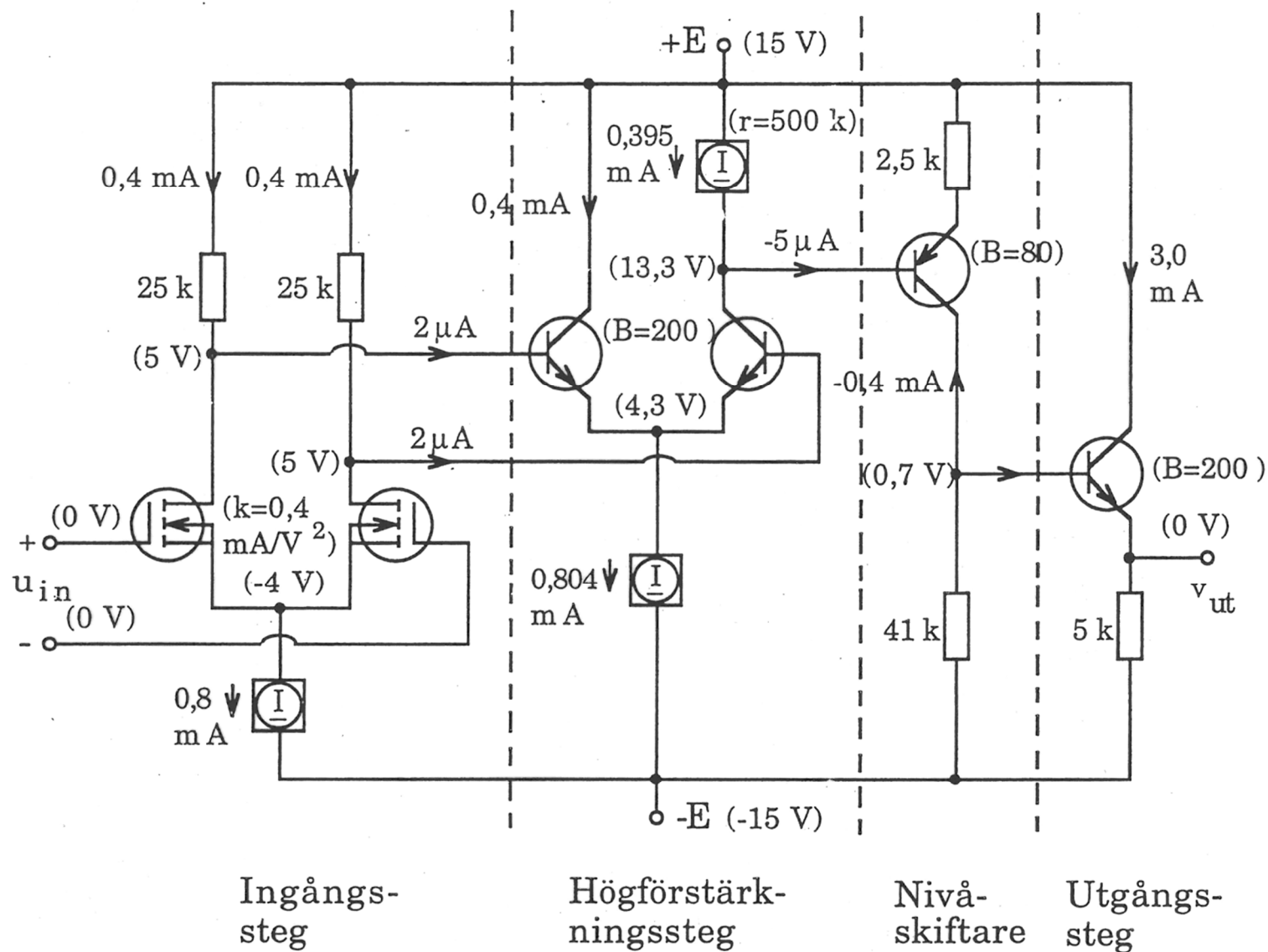
Bipolartransistorer - Inledning

Mikael Olofsson

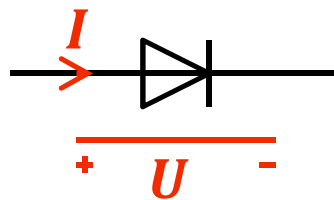
Institutionen för Systemteknik (ISY)

Ämnesområdet Elektroniska kretsar och system

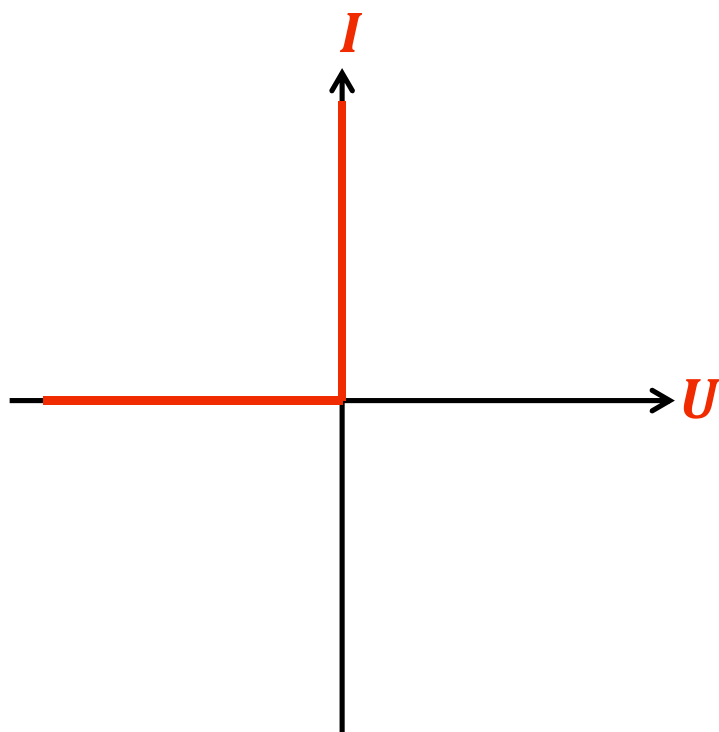
Operationsförstärkare



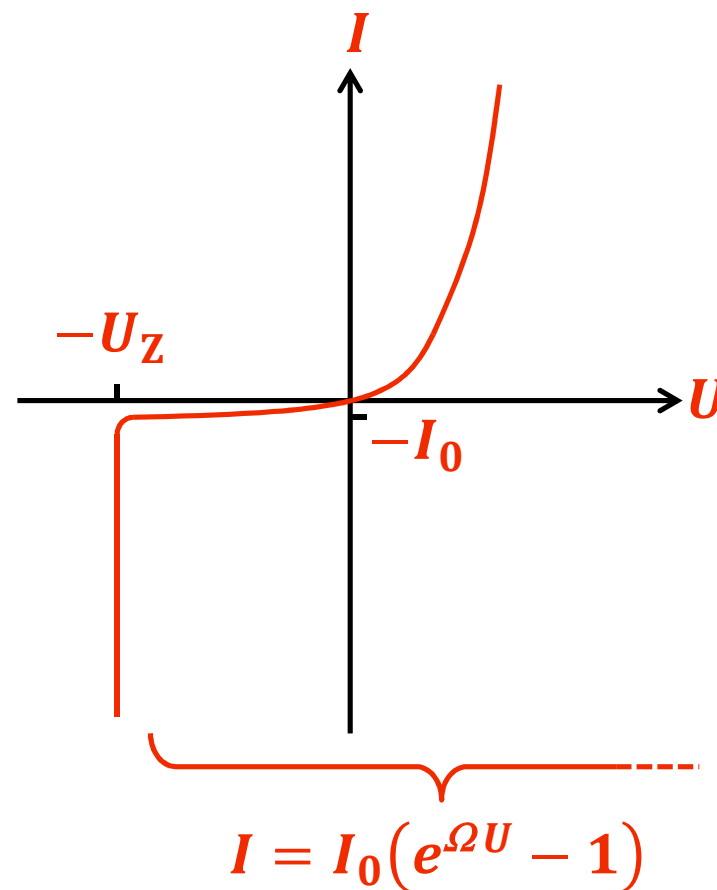
Dioder



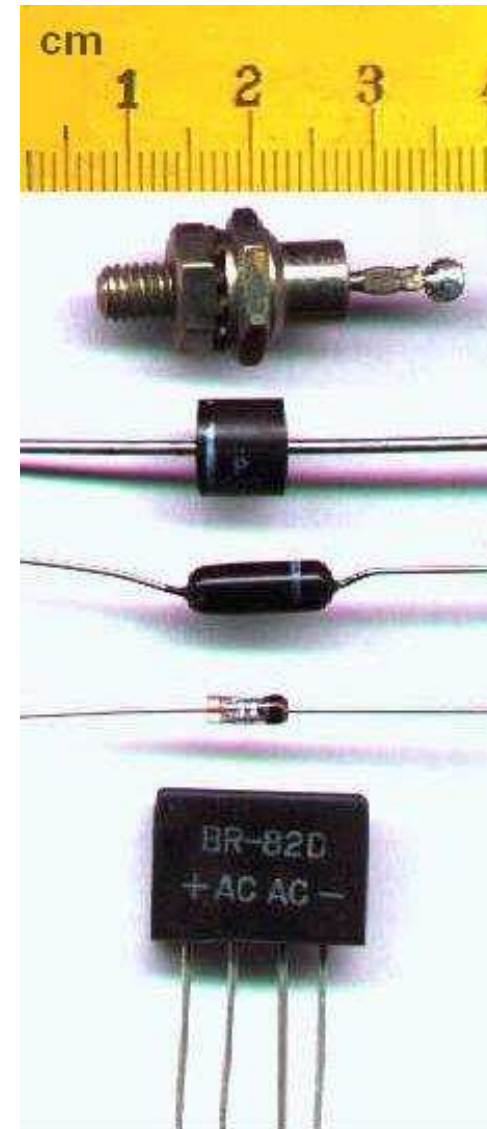
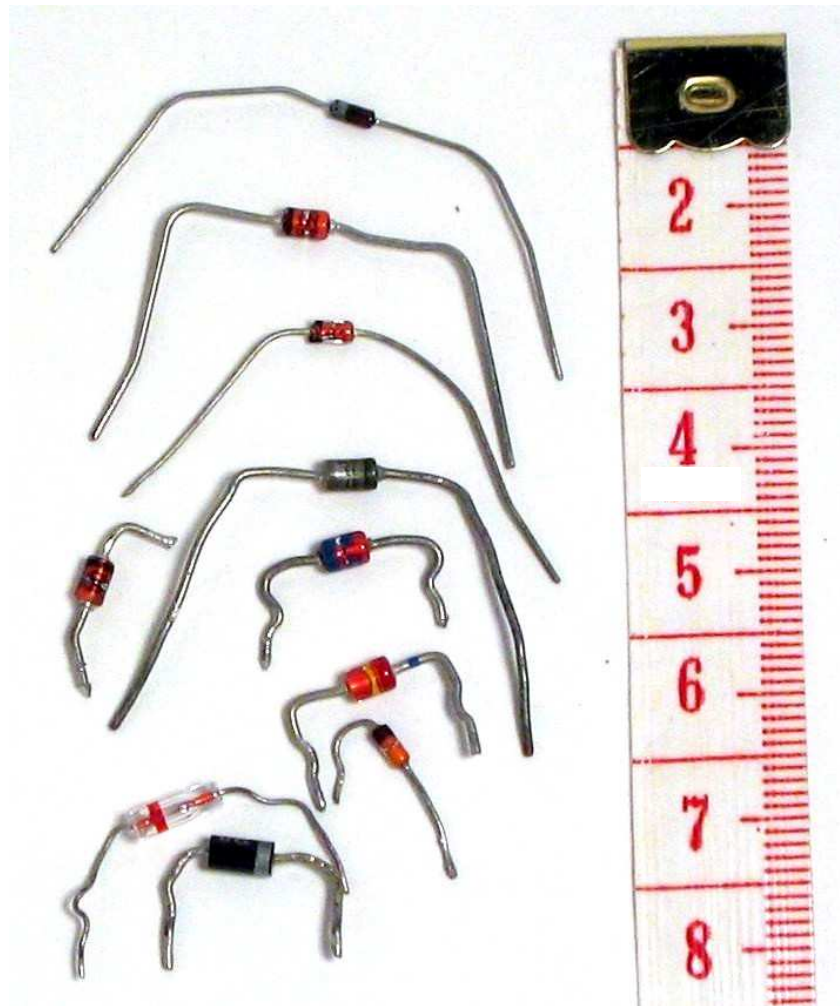
Ideal diod



Verklig diod



Dioder – Exempel

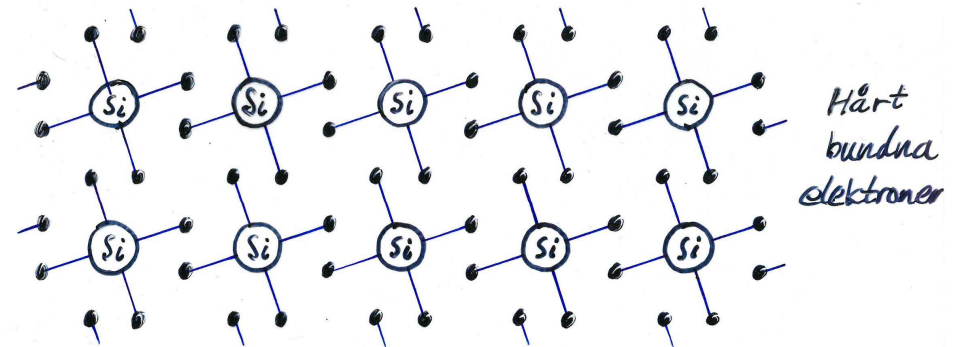


Källa: Wikipedia

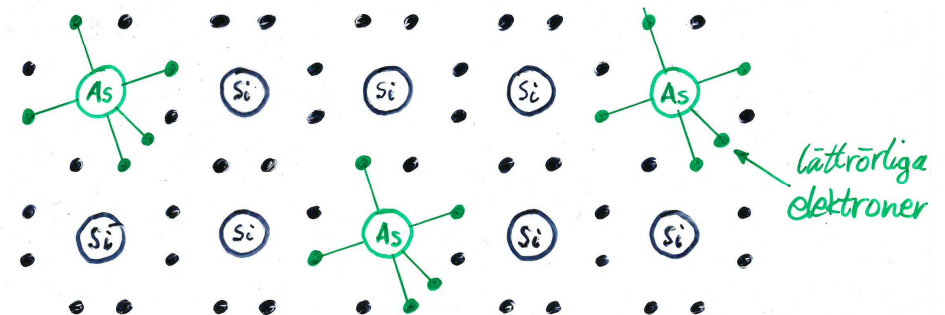
Halvledare

	3 A	4 A	5 A	
	3 5B Bor Boron 10.811	$\pm 4, 2$ 6C Kol Carbon 12.0111	$\pm 3, 5, 4, 2$ 7N Kväve Nitrogen 14.0067	
	3 13Al Aluminium Aluminum 26.9815	4 14Si Kisel Silicon 28.086	$\pm 3, 4, 5$ 15P Fosfor Phosphorus 30.9738	6,
2 8 18 2	3 31Ga Gallium 69.72	4 32Ge Germanium 72.59	$\pm 3, 5$ 33As Arsenik Arsenic 74.9216	3 S
2 8 18 18 2	3 49In Indium 114.82	4, 2 50Sn Tenn Tin 118.69	$\pm 3, 5$ 51Sb Antimon Antimony 121.75	5 T
2 8 18 32 18 2	3, 1 81Tl Tallium Thallium 204.37	4, 2 82Pb Bly Lead 207.19	3, 5 83Bi Vismut Bismuth 208.980	8 P

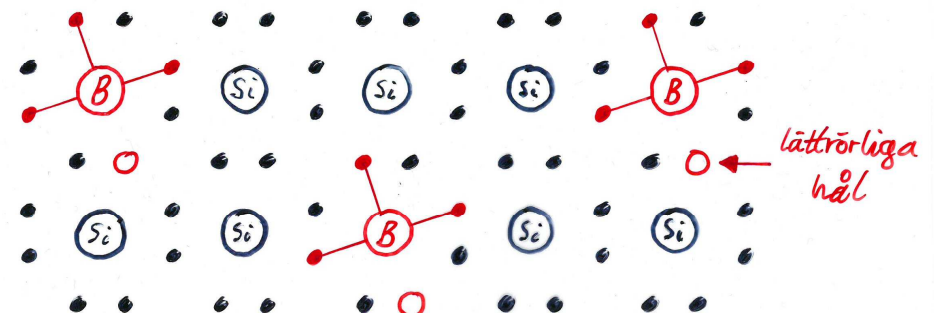
Kiselkristall



N-dopad kristall

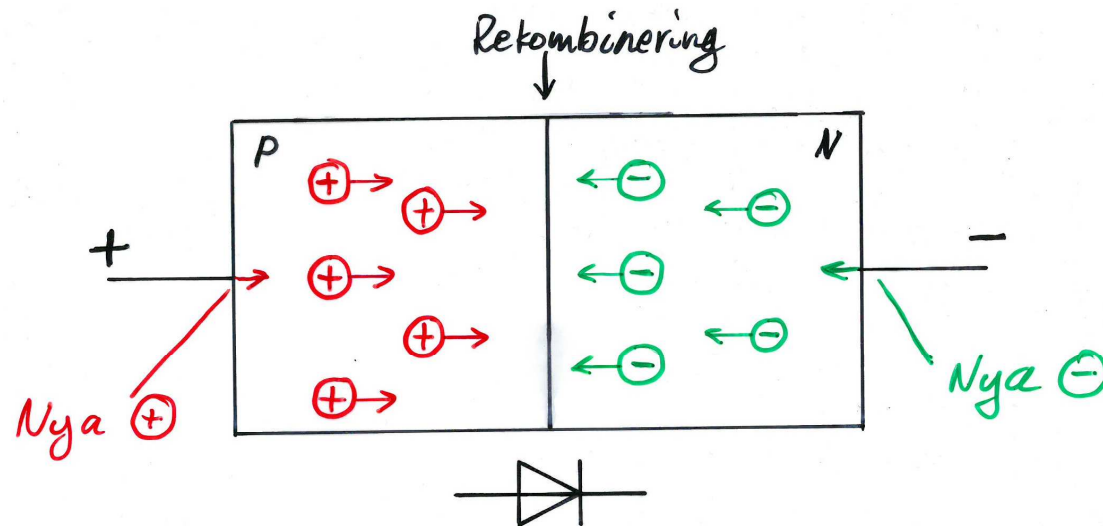


P-dopad kristall

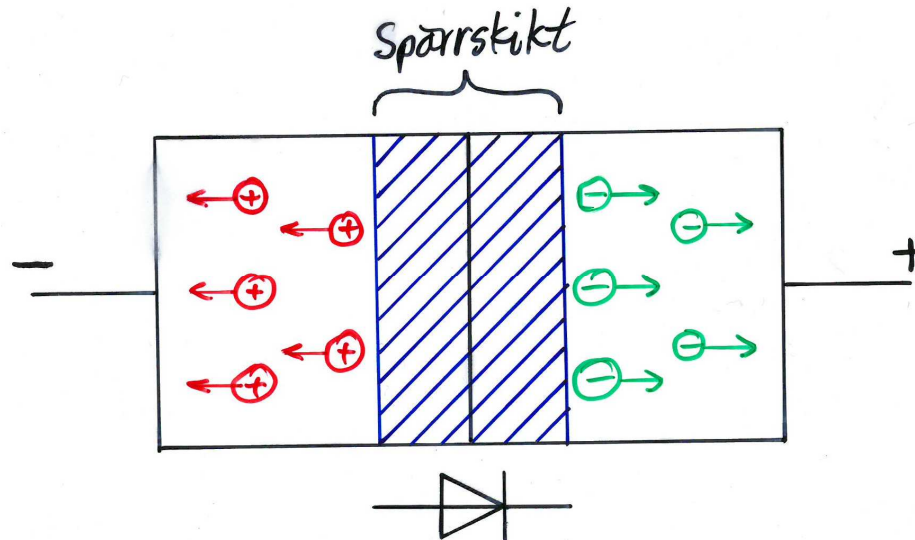


Diodens funktion

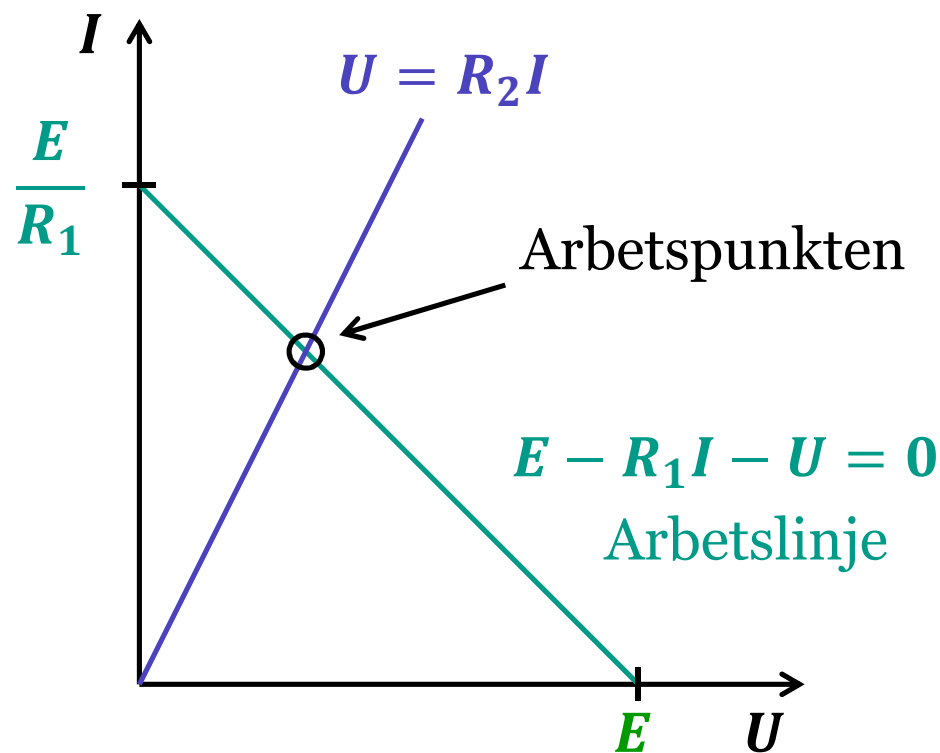
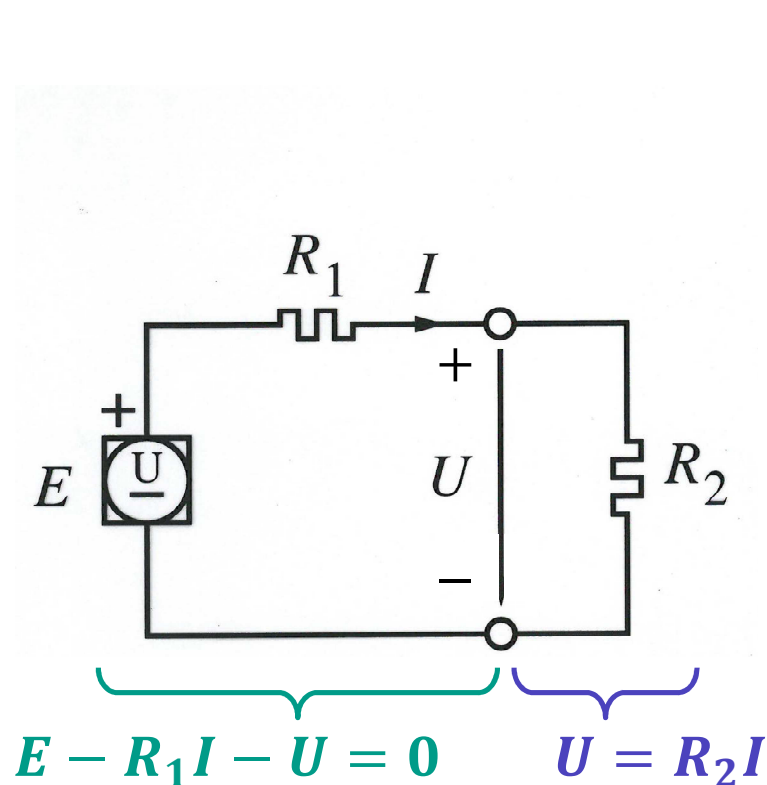
Framspänd diod:



Backspänd diod:



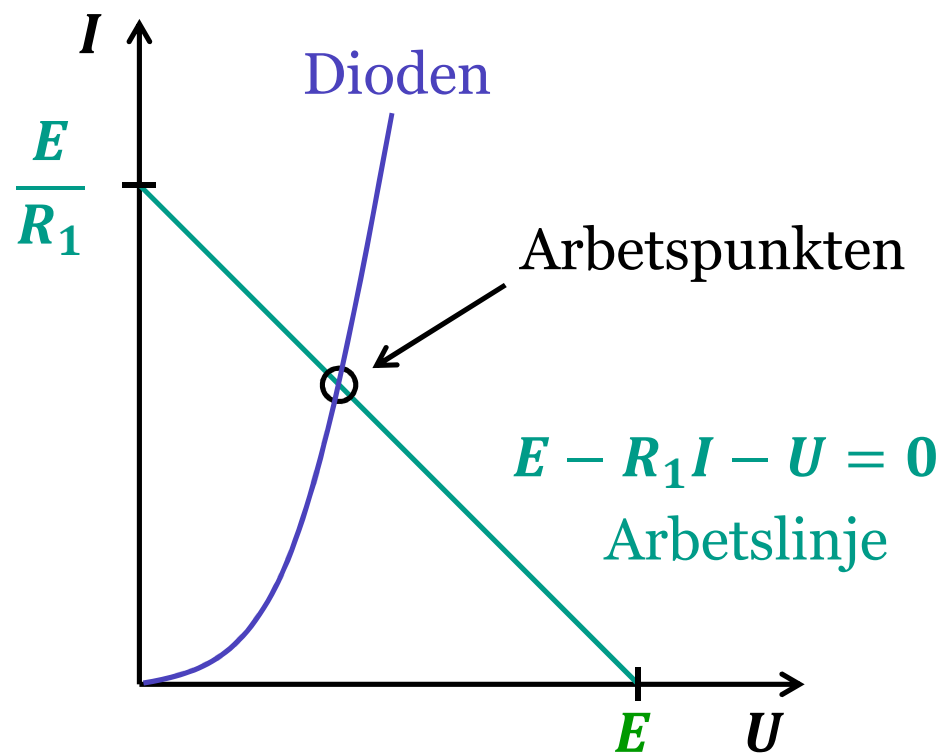
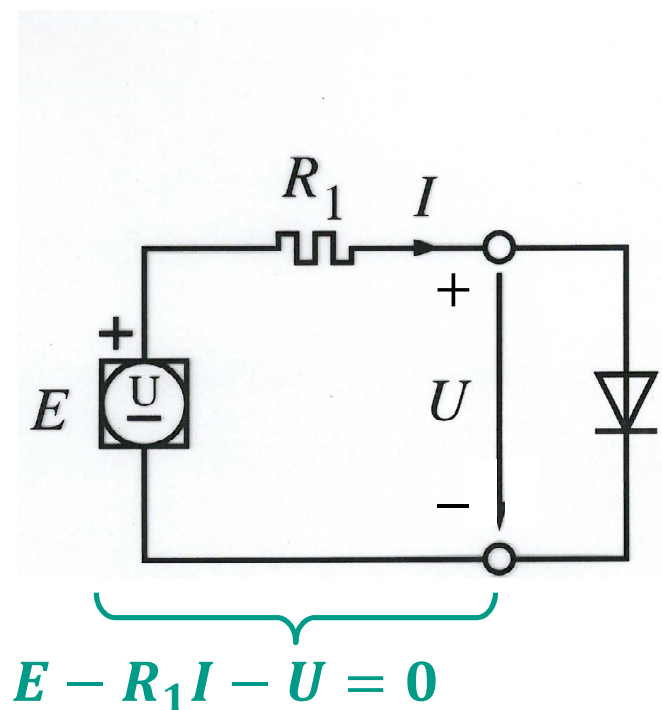
Arbetspunktsbestämning – Introduktion



$$I = \frac{E}{R_1 + R_2}$$

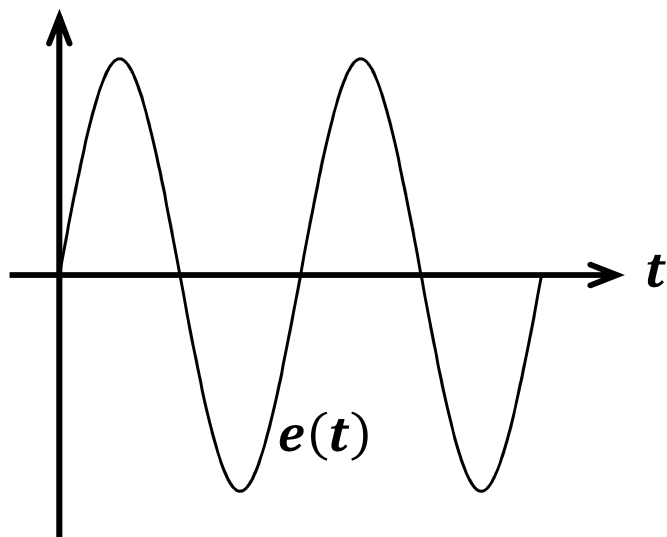
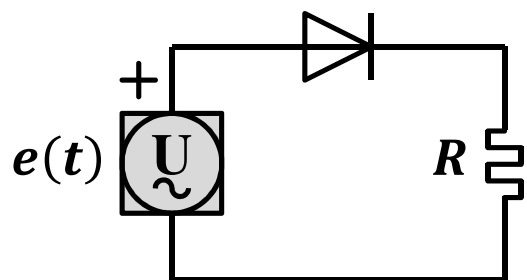
$$U = \frac{R_2}{R_1 + R_2} E$$

Arbetspunktsbestämning för diod

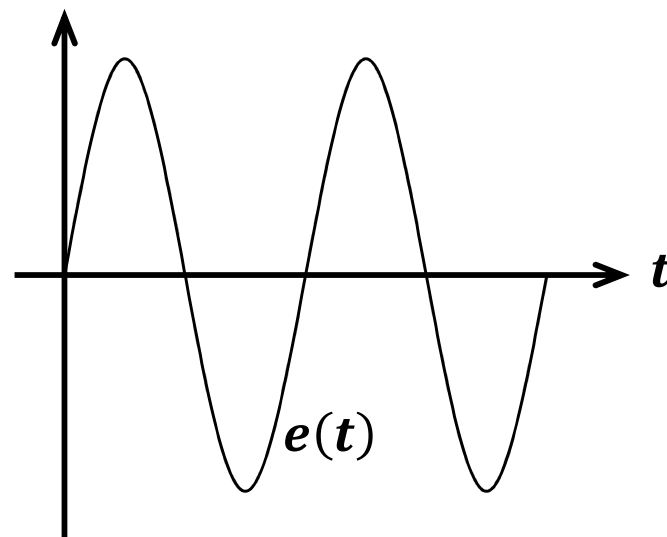
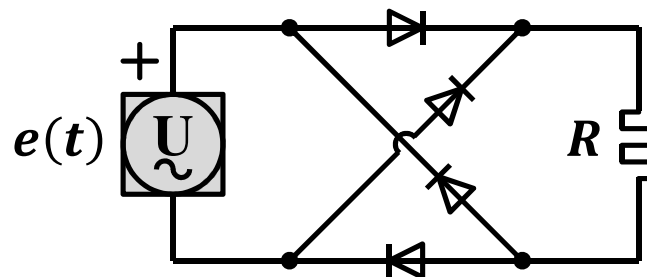


Likriktning med diod 1(3)

Halvvågslikriktning

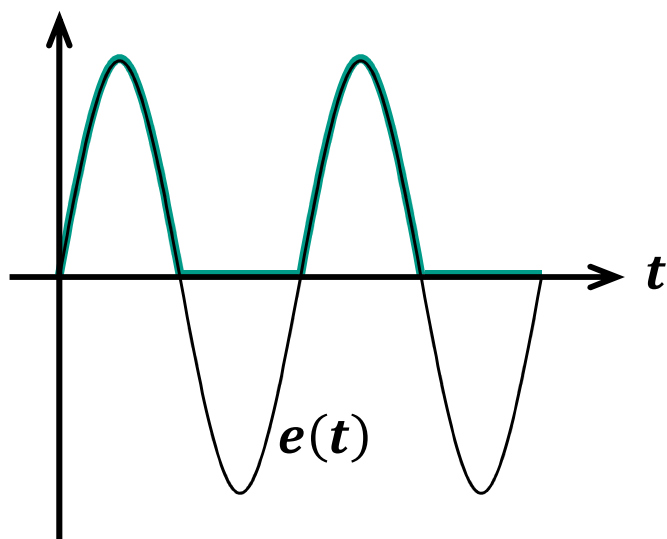
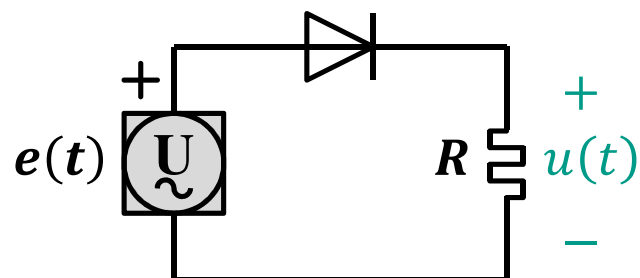


Helvågslikriktning

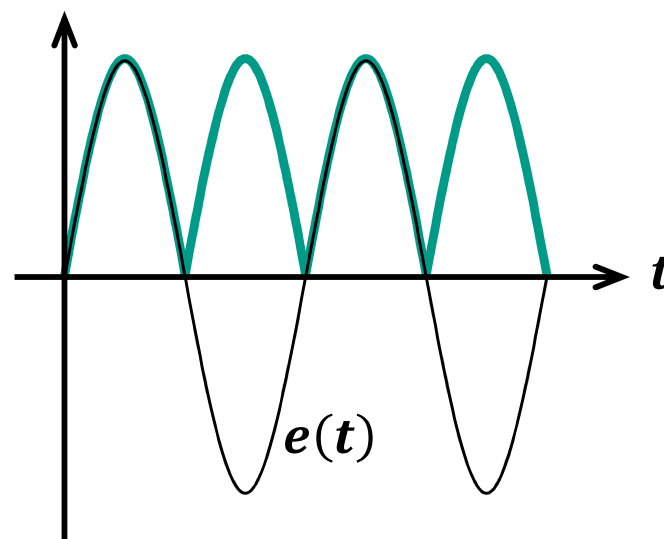
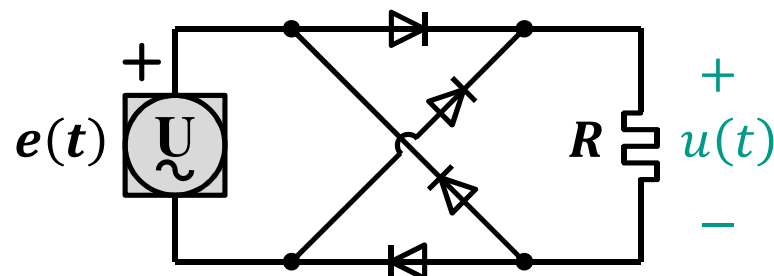


Likriktning med diod 2(3)

Halvvågslikriktning

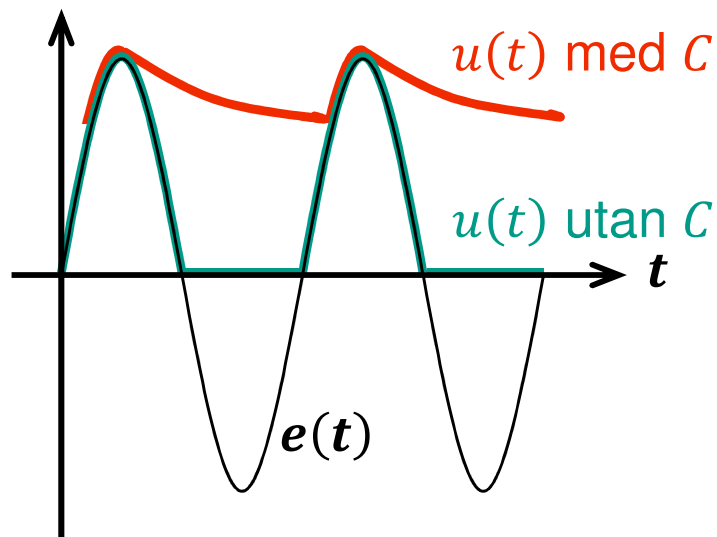
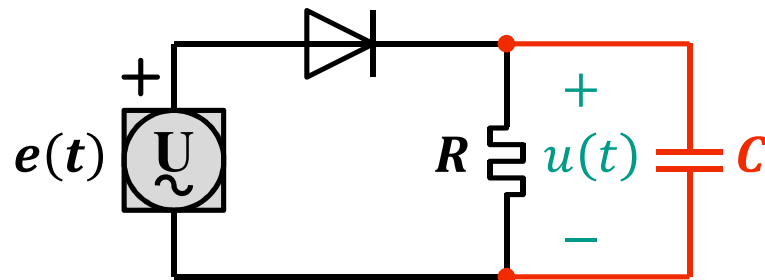


Helvågslikriktning

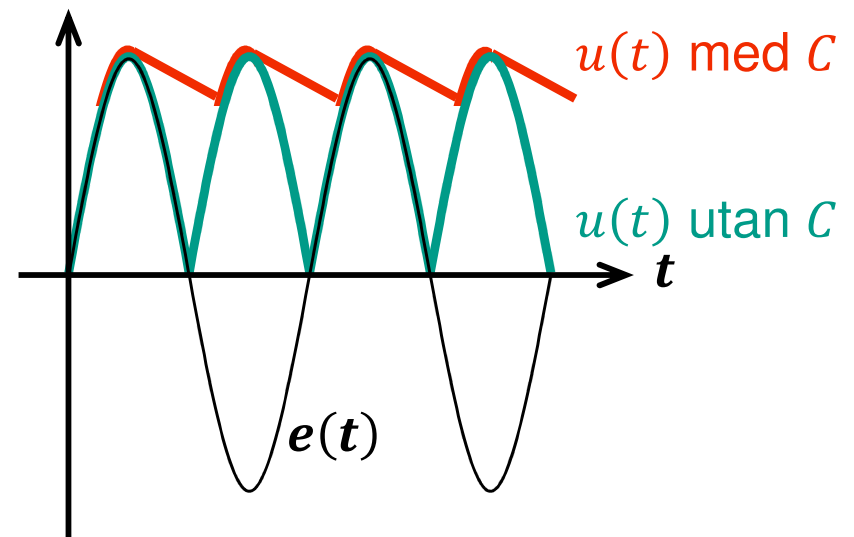
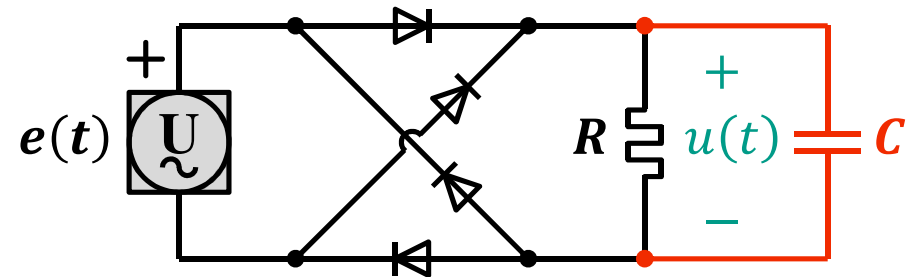


Likriktning med diod 2(3)

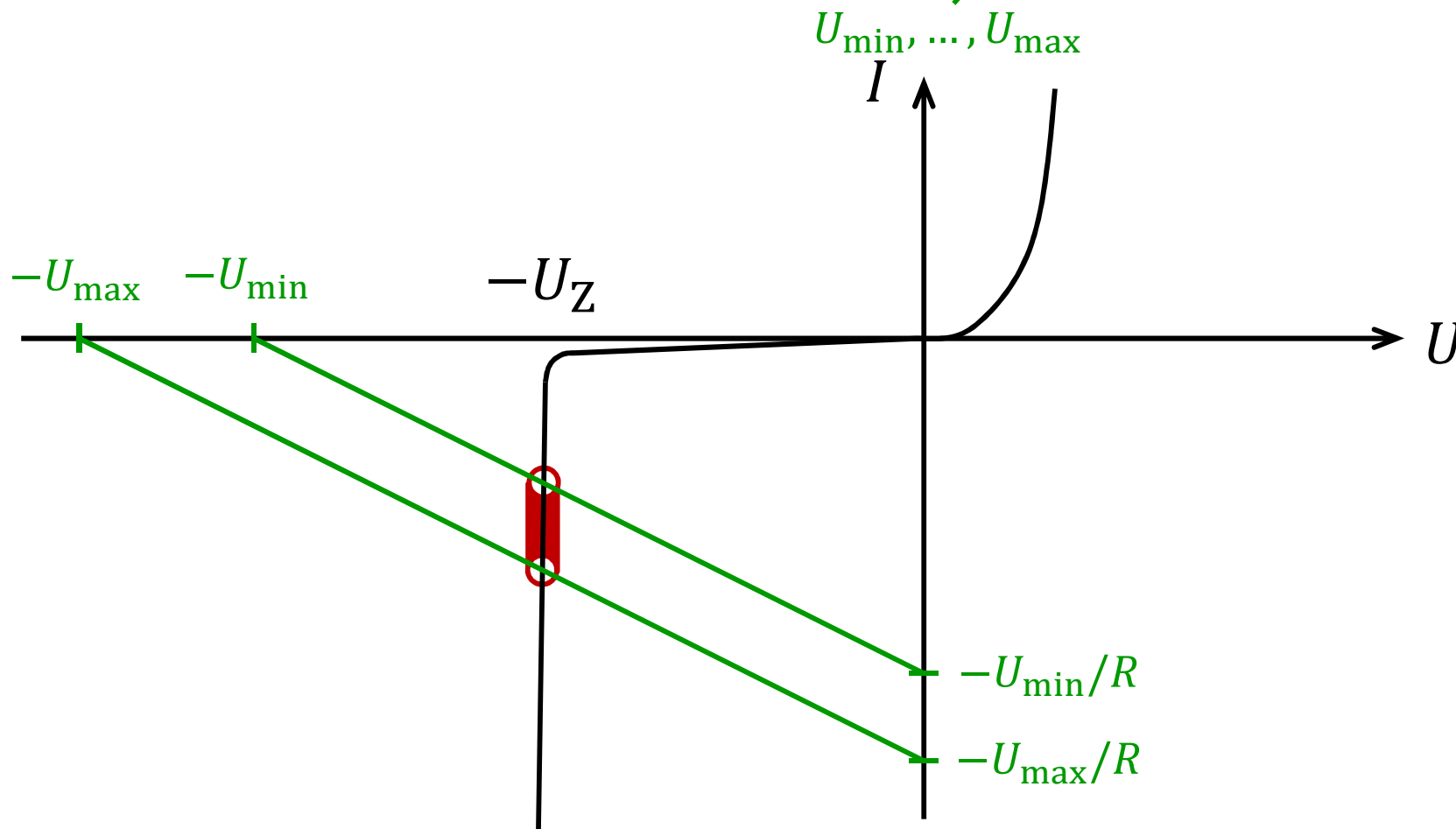
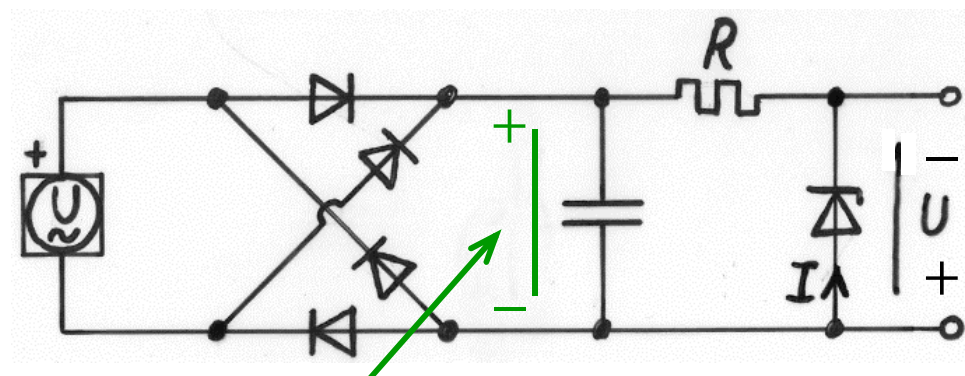
Halvvågslikriktning



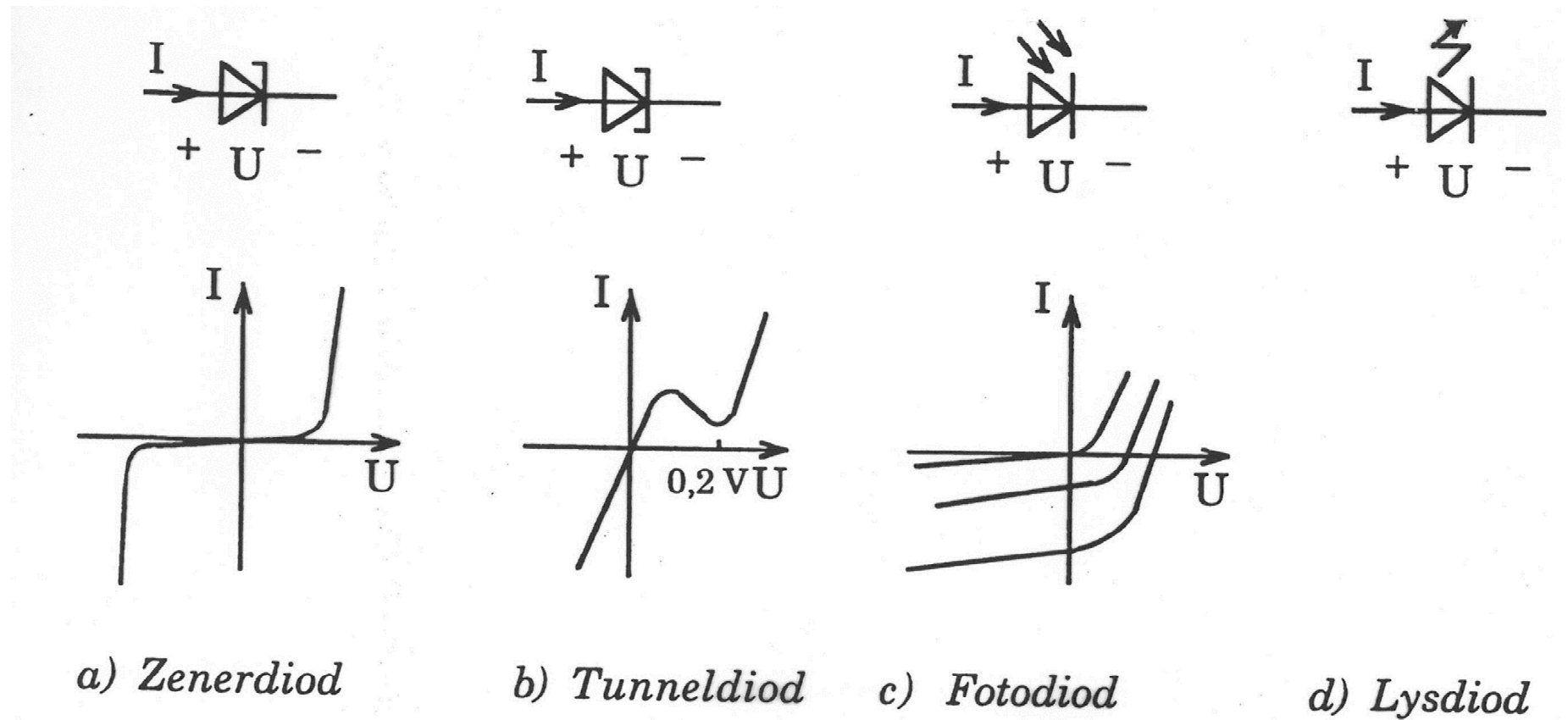
Helvågslikriktning



Stabilisering med zenerdiod



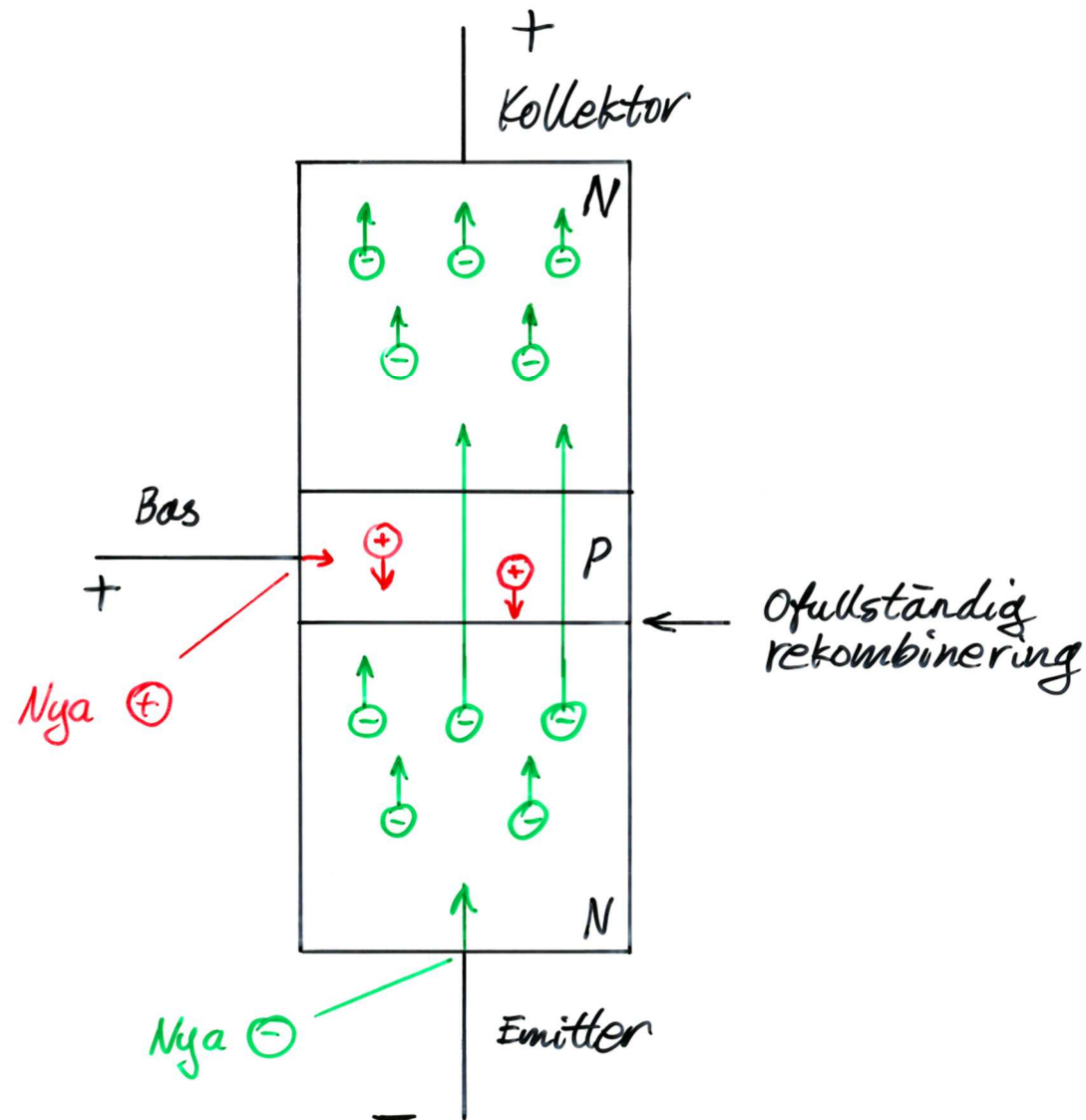
Andra slags dioder



Figur 3.72 Symbol och karaktäristik för några olika diodtyper.

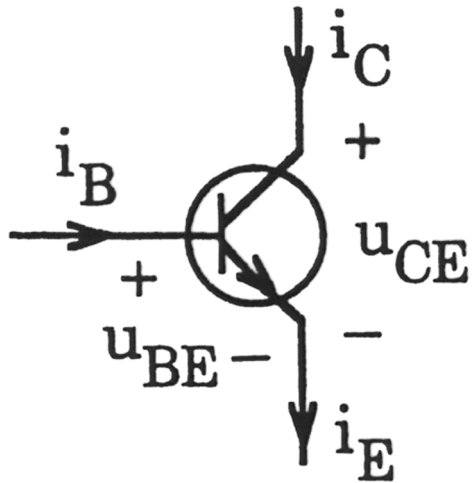
Figur 3.72 ur Söderkvist

Bipolartransistorn - NPN



Bipolartransistorer – Variabler och referensriktningar

NPN-transistor



Krav

Positiva strömmar
och spänningar

Grundekvationer

Strömförstärkning

$$i_C = B i_B$$

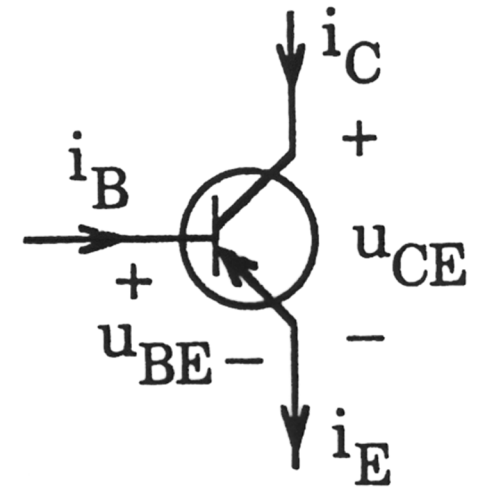
Strömförstärkningsfaktor

$$5 < B < 1000$$

Kirchhoffs strömlag

$$i_E = i_C + i_B$$

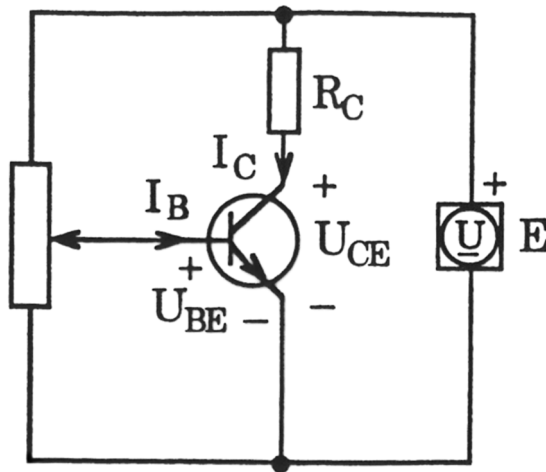
PNP-transistor



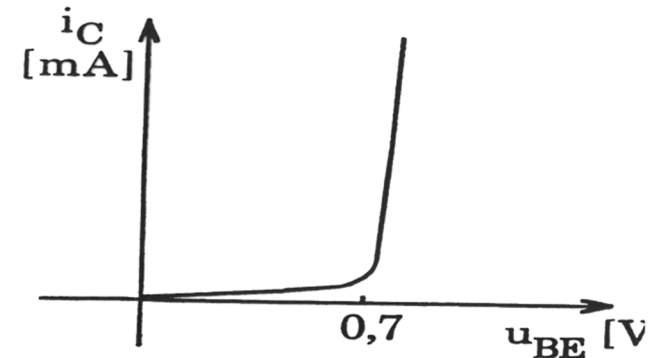
Krav

Negativa strömmar
och spänningar

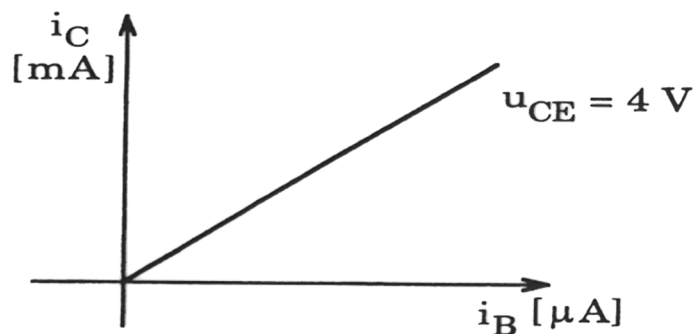
Bipolartransistorer – Några samband



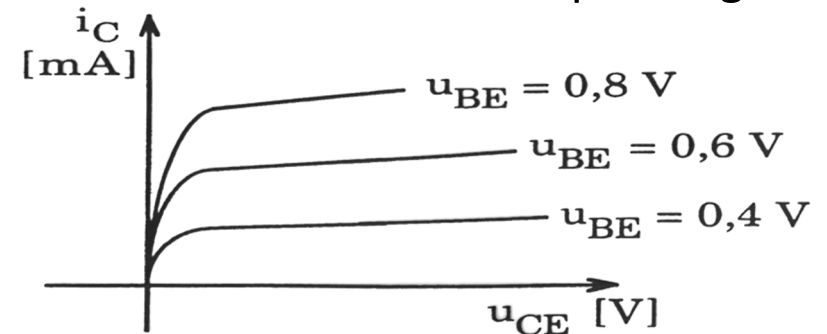
Kollektorström som funktion
av bas-emitter-spänning



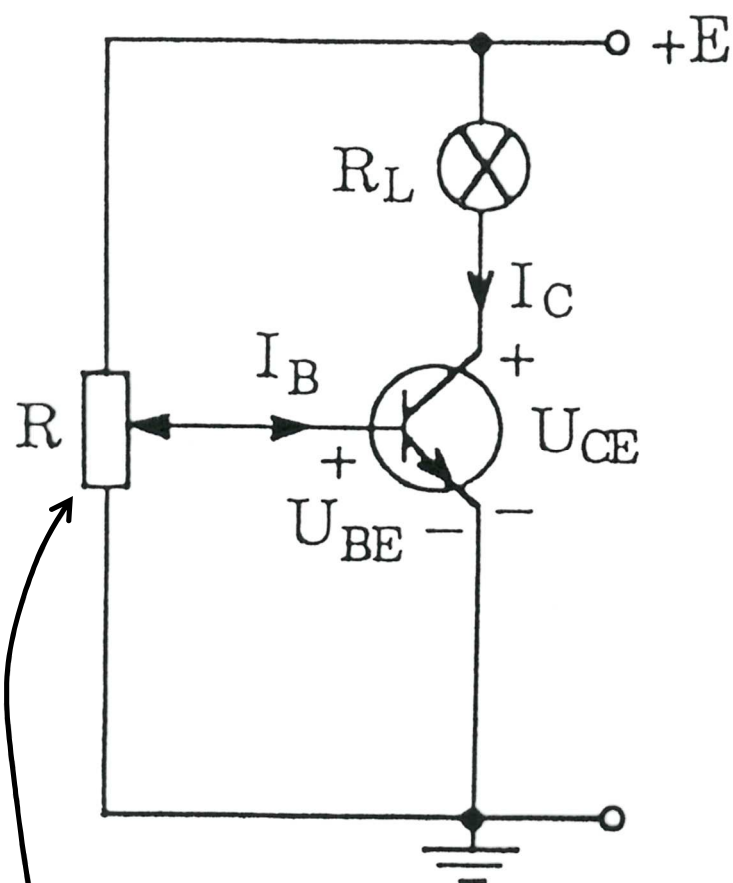
Kollektorström som funktion
av basström



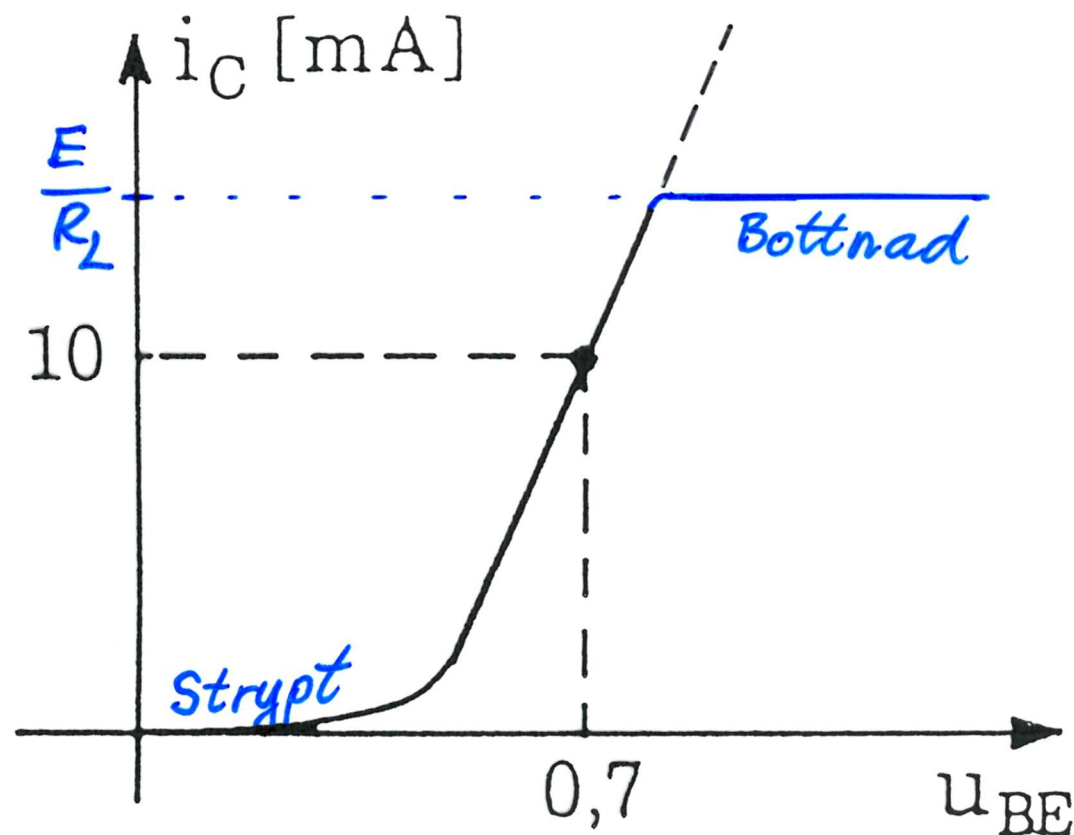
Kollektorström som funktion
av kollektor-emitter-spänning



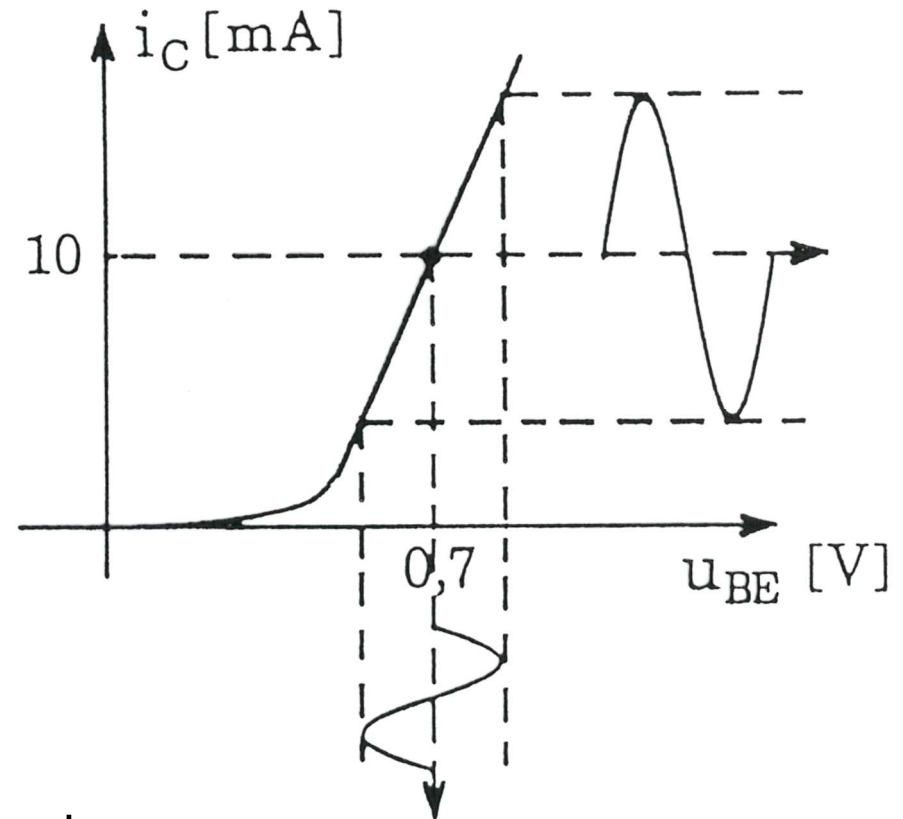
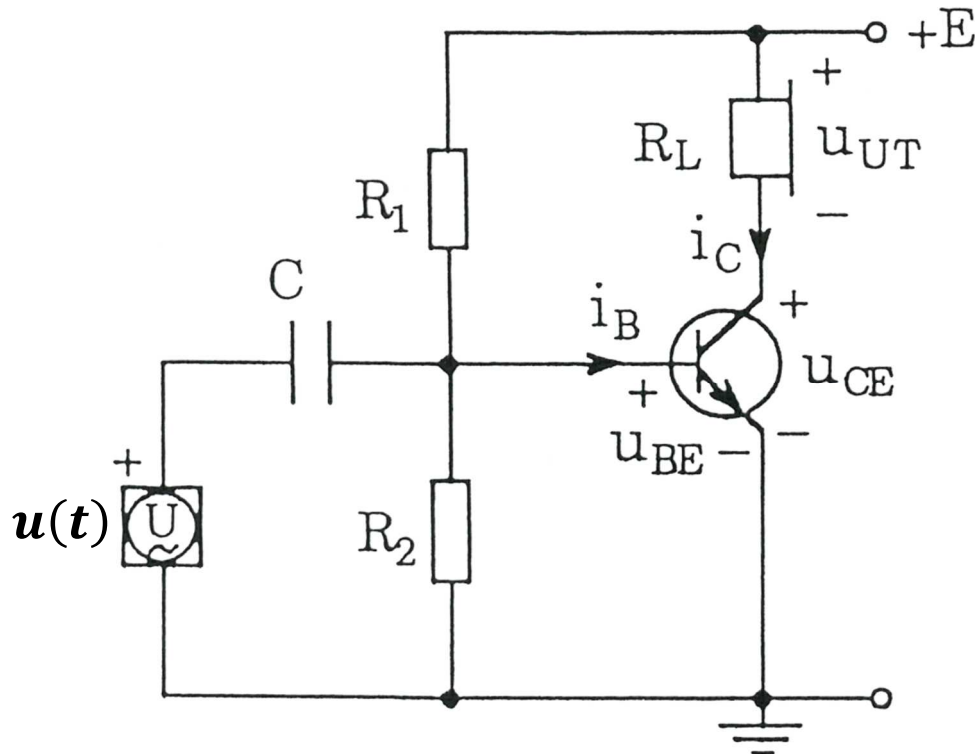
Strömstyrning med NPN-transistor



Potentiometer (vridmotstånd)



Förstärkning av signalspänning



Obs! Signalspänningen $u_{be}(t) = u(t)$ om C är stor.

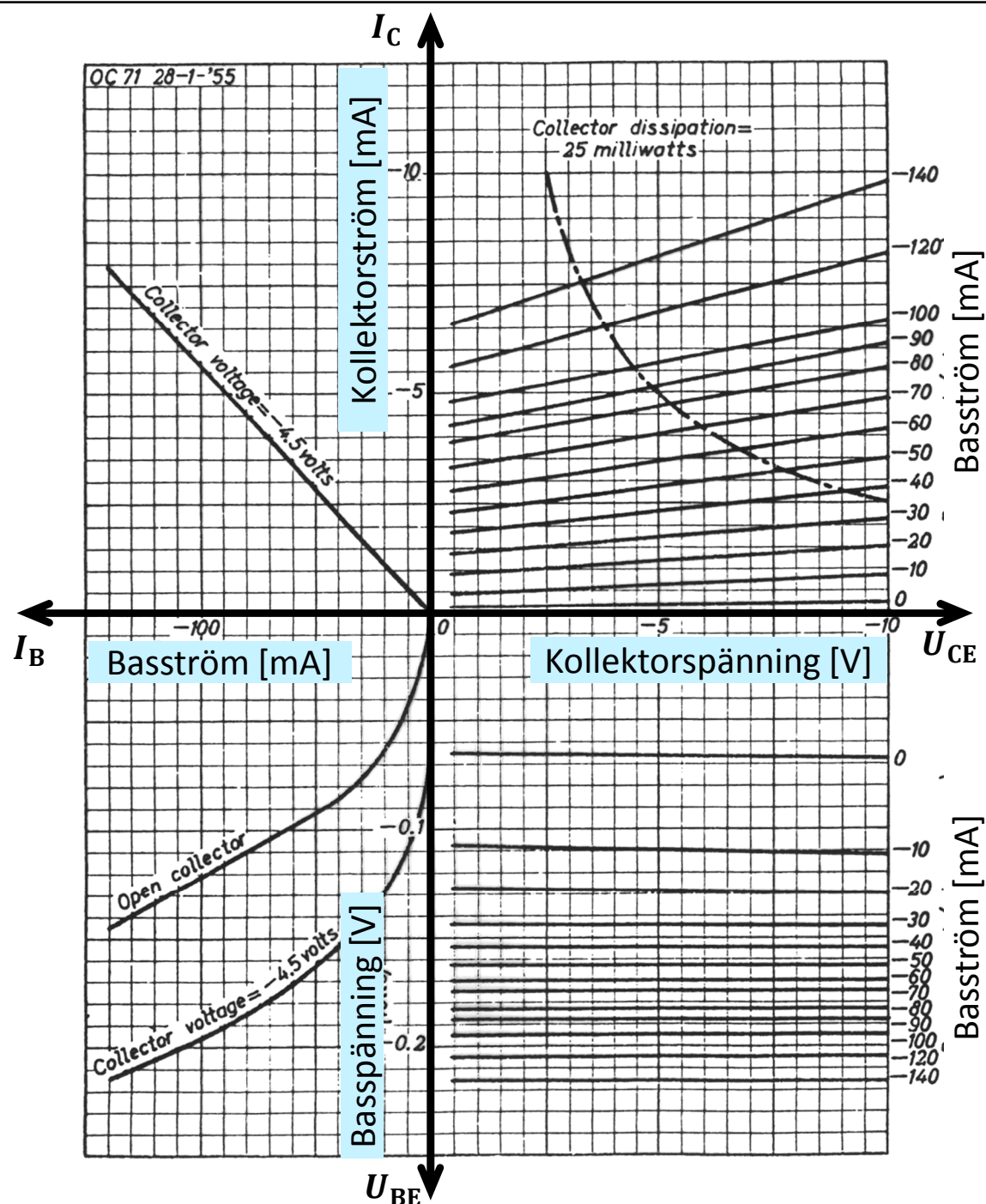
$$u_{BE}(t) = U_{BEQ} + u_{be}(t)$$

$$i_C(t) = I_{CQ} + i_c(t)$$

$$u_{UT}(t) = R_L i_c(t)$$

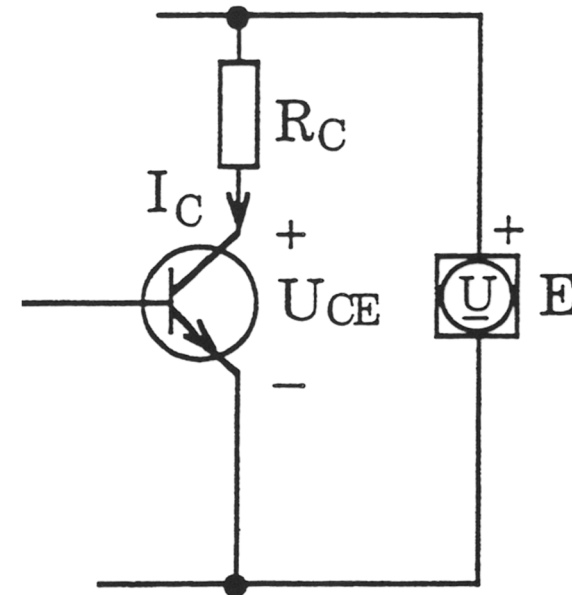
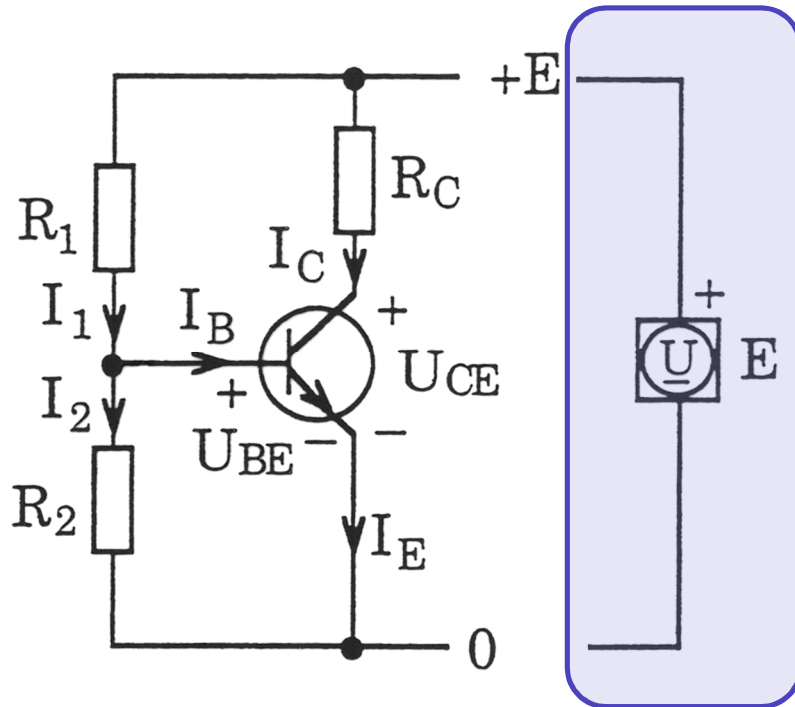
Fullständigt kurvblad för PNP-transistor

Observera: Fyra diagram i ett.
Varje kvadrant är ett separat
diagram



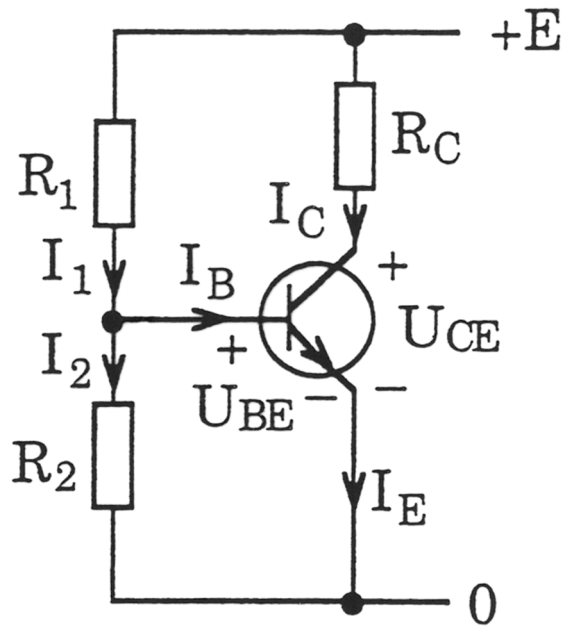
Enkel transistorkoppling – Arbetslinje

Underförstått

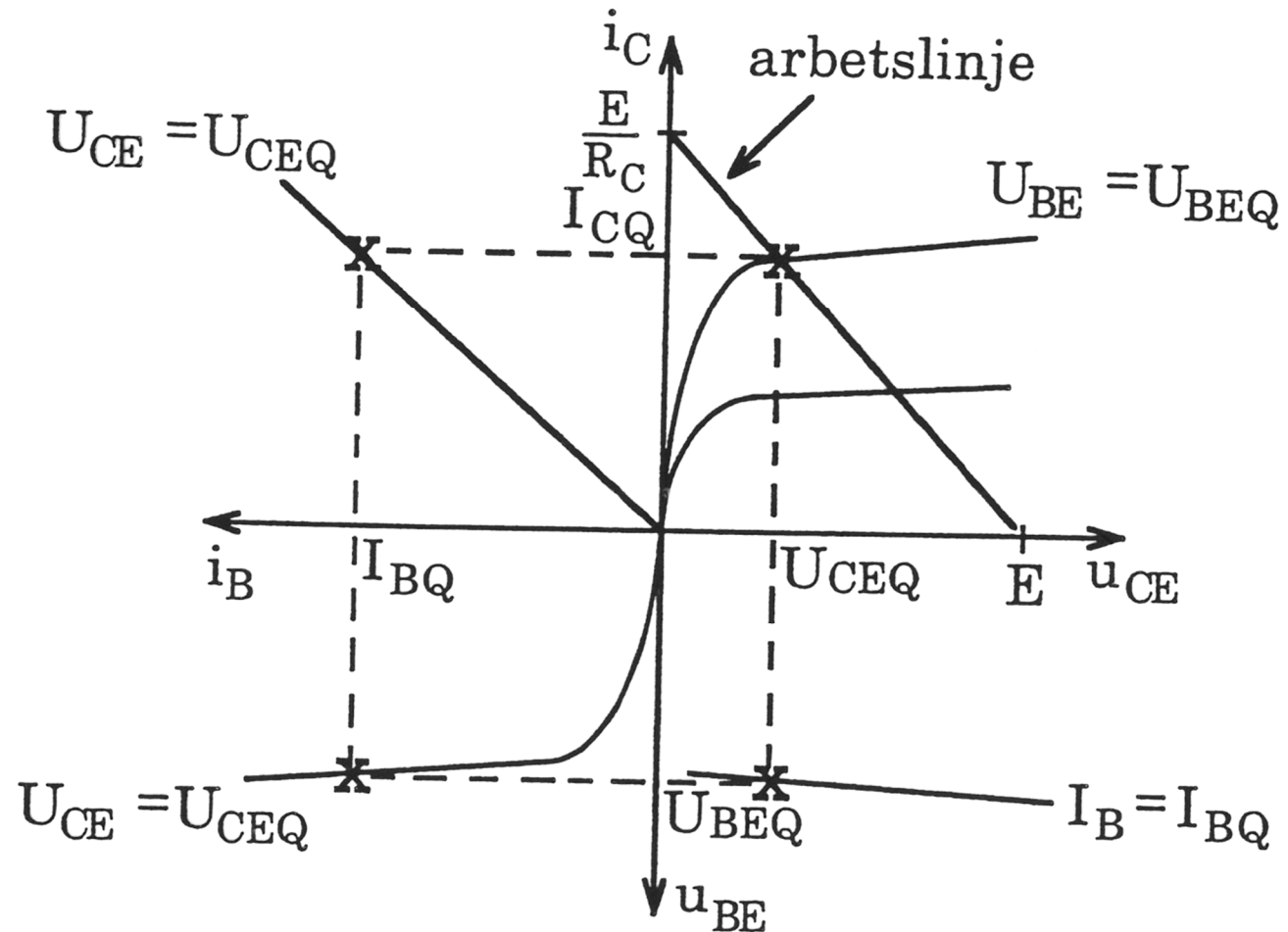


$$\text{KVL: } E - R_C I_C - U_{CE} = 0$$

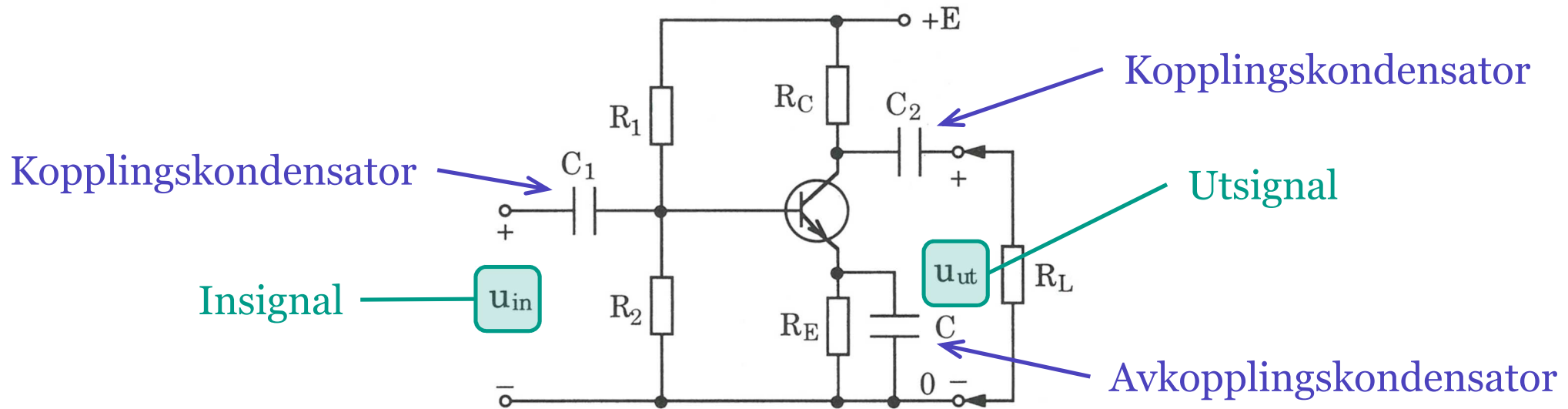
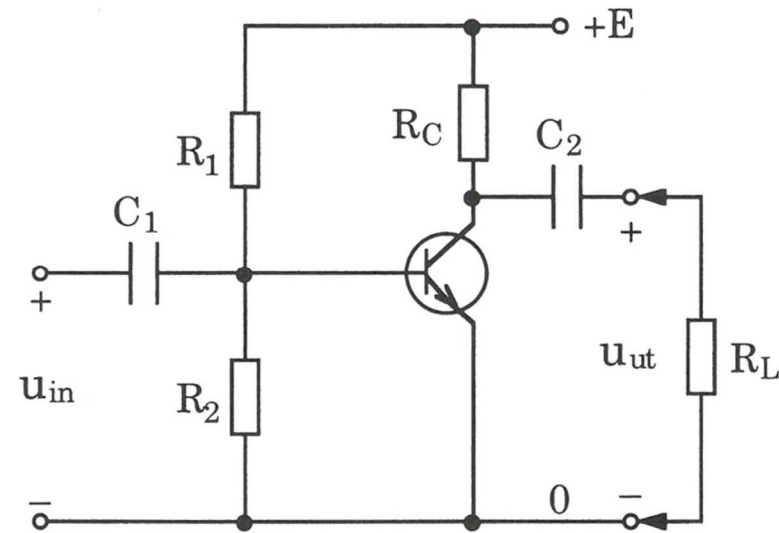
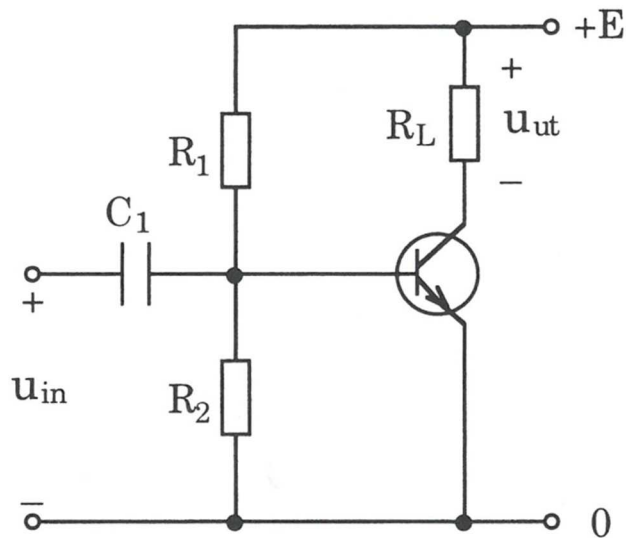
Enkel transistorkoppling – Arbetspunkt



$$E - R_C I_C - U_{CE} = 0$$



GE-steg – Gemensam emitter



Mikael Olofsson
ISY/EKS

www.liu.se